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## **CLAIMS**

1. A developer composition for resists, comprising an organic quaternary ammonium base as a main component and a surfactant,

said surfactant containing an anionic surfactant represented by the following general formula (I):

$$R_1$$
 $R_2$ 
 $R_3$ 
 $R_4$ 
 $R_5$ 

wherein at least one member of  $R_1$  and  $R_2$  represents an alkyl or alkoxy group having 5 to 18 carbon atoms and any reminder member represents a hydrogen atom, or an alkyl or alkoxy group having 5 to 18 carbon atoms, and at least one member of  $R_3$ ,  $R_4$  and  $R_5$  represents a group represented by the following general formula (II):

$$-SO_3M \cdot \cdot \cdot (II)$$

wherein M represents a metal atom, and any reminder member represent a hydrogen atom or a group represented by the above general formula (II).

2. The developer composition for resists according to claim 1, wherein, in the general formula (II), M represents one selected from sodium, potassium and calcium, provided that, in the general formula (I), when two or more groups represented by the general formula (II) are present, M may be the same or different.

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3. A method for formation of a resist pattern, comprising applying a resist composition on a substrate to form a resist layer, prebaking the resist layer, selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to any one of claims 1 to 2 to form a resist pattern.